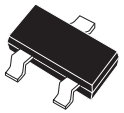
CMPT930

NPN SILICON TRANSISTOR



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPT930 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for small signal general purpose amplifier applications.
Marking Code is C1X.

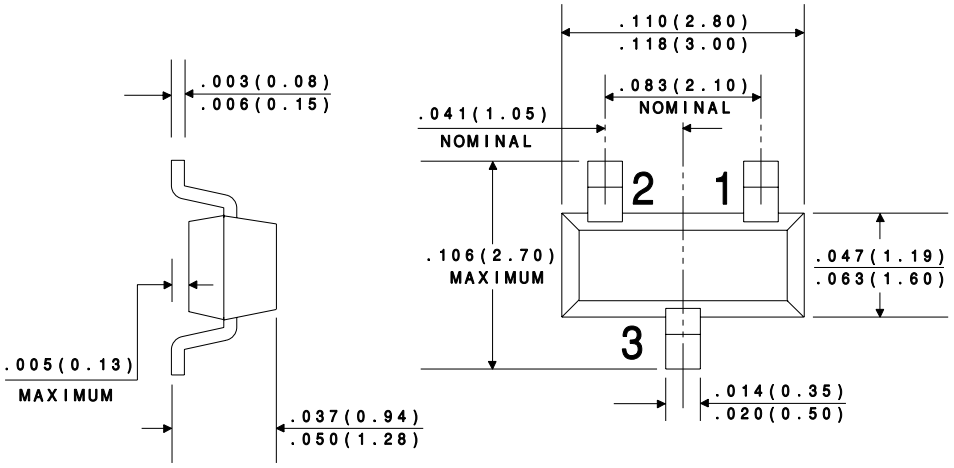
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	45	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Collector Current	I_C	30	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	V_{CB}=45V		10	nA
I_{CEO}	V_{CE}=5.0V		10	nA
I_{CES}	V_{CE}=45V		10	nA
I_{EBO}	V_{EB}=5.0V		10	nA
BV_{CBO}	I_C=10μA	45		V
BV_{CEO}	I_C=10mA	45		V
BV_{EBO}	I_E=10μA	5.0		V
$V_{CE(SAT)}$	I_C=10mA, I_B=0.5mA		1.0	V
$V_{BE(SAT)}$	I_C=10mA, I_B=0.5mA	0.6	1.0	V
h_{FE}	V_{CE}=5.0V, I_C=10μA	100	300	
h_{FE}	V_{CE}=5.0V, I_C=500μA	150		
h_{FE}	V_{CE}=5.0V, I_C=10mA		600	
f_T	V_{CE}=5.0V, I_C=500mA, f=30MHz	30		MHz
C_{ob}	V_{CB}=5.0V, I_E=0, f=1.0MHz		8.0	pF
NF	V_{CE}=5.0V, I_C=10mA, R_S=10kΩ, f=10Hz to 15.7kHz		3.0	dB

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR

R2

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